

# NTLJD3183CZ

## Power MOSFET

20 V/–20 V, 4.7 A/–4.0 A, Complementary,  
2x2 mm, WDFN Package

### Features

- WDFN 2x2 mm Package with Exposed Drain Pads for Excellent Thermal Conduction
- Lowest  $R_{DS(on)}$  in 2x2 mm Package
- Footprint Same as SC–88 Package
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments
- ESD Protected
- This is a Pb–Free Device

### Applications

- Optimized for Battery and Load Management Applications in Portable Equipment
- Load Switch
- Level Shift Circuits
- DC–DC Converters

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain–to–Source Voltage		$V_{DSS}$	20	V	
Gate–to–Source Voltage		$V_{GS}$	$\pm 8.0$	V	
N–Channel Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	3.8	A
		$T_A = 85^\circ\text{C}$		2.7	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$		4.7	
P–Channel Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	–3.2	A
		$T_A = 85^\circ\text{C}$		–2.3	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$		–4.0	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	1.5	W
		$t \leq 5$ s		2.3	
N–Channel Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	2.6	A
		$T_A = 85^\circ\text{C}$		1.9	
P–Channel Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	–2.2	A
		$T_A = 85^\circ\text{C}$		–1.6	
Power Dissipation (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	0.71	W
Pulsed Drain Current	N–Ch	$t_p = 10$ $\mu\text{s}$	$I_{DM}$	18	A
	P–Ch			–16	
Operating Junction and Storage Temperature		$T_J, T_{STG}$	–55 to 150	$^\circ\text{C}$	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

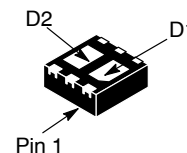
1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz Cu.



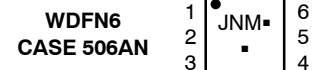
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
N–Channel 20 V	68 m $\Omega$ @ 4.5 V	4.7 A
	86 m $\Omega$ @ 2.5 V	4.2 A
	120 m $\Omega$ @ 1.8 V	3.5 A
P–Channel –20 V	100 m $\Omega$ @ –4.5 V	–4.0 A
	144 m $\Omega$ @ –2.5 V	–3.3 A
	200 m $\Omega$ @ –1.8 V	–2.8 A

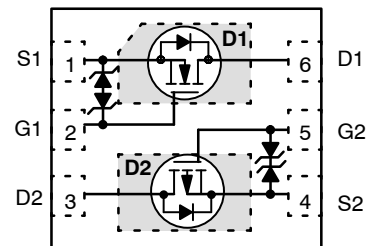


### MARKING DIAGRAM



JN = Specific Device Code  
M = Date Code  
▪ = Pb–Free Package  
(Note: Microdot may be in either location)

### PIN CONNECTIONS



(Top View)

### ORDERING INFORMATION

Device	Package	Shipping†
NTLJD3183CZTAG	WDFN6 (Pb–Free)	3000/Tape & Reel
NTLJD3183CZTBG	WDFN6 (Pb–Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTLJD3183CZ

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
<b>SINGLE OPERATION (SELF-HEATED)</b>			
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	83	°C/W
Junction-to-Ambient – Steady State Min Pad (Note 4)	$R_{\theta JA}$	177	
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	54	
<b>DUAL OPERATION (EQUALLY HEATED)</b>			
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	58	°C/W
Junction-to-Ambient – Steady State Min Pad (Note 4)	$R_{\theta JA}$	133	
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	40	

- Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
- Surface Mounted on FR4 Board using the minimum recommended pad size (30 mm<sup>2</sup>, 2 oz Cu).

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	N	$V_{GS} = 0\text{ V}$	$I_D = 250\ \mu\text{A}$	20		V
		P		$I_D = -250\ \mu\text{A}$	-20		
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	N	Ref to $25^\circ\text{C}$	$I_D = 250\ \mu\text{A}$		15	mV/°C
		P		$I_D = -250\ \mu\text{A}$		13	
Zero Gate Voltage Drain Current	$I_{DSS}$	N	$V_{GS} = 0\text{ V}, V_{DS} = 16\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	$\mu\text{A}$
		P	$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$			-1.0	
		N	$V_{GS} = 0\text{ V}, V_{DS} = 16\text{ V}$	$T_J = 85^\circ\text{C}$		10	
		P	$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$			-10	
Gate-to-Source Leakage Current	$I_{GSS}$	N	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8.0\text{ V}$			$\pm 10$	$\mu\text{A}$
		P				$\pm 10$	

## ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	N	$V_{GS} = V_{DS}$	$I_D = 250\ \mu\text{A}$	0.4		1.0	V
		P		$I_D = -250\ \mu\text{A}$	-0.4		-1.0	
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	N	Ref to $25^\circ\text{C}$	$I_D = 250\ \mu\text{A}$		-3.0	mV/°C	
		P		$I_D = -250\ \mu\text{A}$		2.0		
Drain-to-Source On Resistance	$R_{DS(on)}$	N	$V_{GS} = 4.5\text{ V}, I_D = 2.0\text{ A}$		34	68	mΩ	
		P	$V_{GS} = -4.5\text{ V}, I_D = -2.0\text{ A}$		68	100		
		N	$V_{GS} = 2.5\text{ V}, I_D = 2.0\text{ A}$		42	86		
		P	$V_{GS} = -2.5\text{ V}, I_D = -2.0\text{ A}$		90	144		
		N	$V_{GS} = 1.8\text{ V}, I_D = 1.7\text{ A}$		53	120		
		P	$V_{GS} = -1.8\text{ V}, I_D = -1.7\text{ A}$		125	200		
Forward Transconductance	$g_{FS}$	N	$V_{DS} = 5.0\text{ V}, I_D = 2.0\text{ A}$		7.0		S	
		P	$V_{DS} = -5.0\text{ V}, I_D = -2.0\text{ A}$		6.5			

# NTLJD3183CZ

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions	Min	Typ	Max	Unit		
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>									
Input Capacitance	C <sub>ISS</sub>	N	f = 1.0 MHz, V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 10 V		355	pF		
		P		V <sub>DS</sub> = -10 V		450			
Output Capacitance	C <sub>OSS</sub>	N		V <sub>DS</sub> = 10 V		70			
		P		V <sub>DS</sub> = -10 V		90			
Reverse Transfer Capacitance	C <sub>RSS</sub>	N		V <sub>DS</sub> = 10 V		50			
		P		V <sub>DS</sub> = -10 V		62			
Total Gate Charge	Q <sub>G(TOT)</sub>	N		V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.8 A		4.6		7.0	nC
		P		V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -10 V, I <sub>D</sub> = -3.8 A		5.2		7.8	
Threshold Gate Charge	Q <sub>G(TH)</sub>	N	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.8 A		0.3				
		P	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -10 V, I <sub>D</sub> = -3.8 A		0.3				
Gate-to-Source Charge	Q <sub>GS</sub>	N	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.8 A		0.6				
		P	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -10 V, I <sub>D</sub> = -3.8 A		0.84				
Gate-to-Drain Charge	Q <sub>GD</sub>	N	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.8 A		1.15				
		P	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -10 V, I <sub>D</sub> = -3.8 A		1.5				

## SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	t <sub>d(ON)</sub>	N	V <sub>GS</sub> = 4.5 V, V <sub>DD</sub> = 5 V, I <sub>D</sub> = 2.0 A, R <sub>G</sub> = 2.0 Ω		6.2		ns
Rise Time	t <sub>r</sub>				5.5		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				15		
Fall Time	t <sub>f</sub>				14		
Turn-On Delay Time	t <sub>d(ON)</sub>	P	V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -5 V, I <sub>D</sub> = -2.0 A, R <sub>G</sub> = 2.0 Ω		6.6		
Rise Time	t <sub>r</sub>				9.0		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				14		
Fall Time	t <sub>f</sub>				12.5		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	N	V <sub>GS</sub> = 0 V, T <sub>J</sub> = 25 °C	I <sub>S</sub> = 1.0 A		0.65	1.0	V	
		P		I <sub>S</sub> = -1.0 A		-0.73	-1.0		
		N	V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	I <sub>S</sub> = 1.0 A		0.55			
		P		I <sub>S</sub> = -1.0 A		-0.62			
Reverse Recovery Time	t <sub>RR</sub>	N	V <sub>GS</sub> = 0 V, dI <sub>S</sub> / dt = 100 A/μs	I <sub>S</sub> = 1.0 A		21	ns		
		P		I <sub>S</sub> = -1.0 A		23			
Charge Time	t <sub>a</sub>	N		I <sub>S</sub> = 1.0 A		10.5			
		P		I <sub>S</sub> = -1.0 A		13			
Discharge Time	t <sub>b</sub>	N		I <sub>S</sub> = 1.0 A		10.5			
		P		I <sub>S</sub> = -1.0 A		10			
Reverse Recovery Charge	Q <sub>RR</sub>	N		I <sub>S</sub> = 1.0 A		7.0			nC
		P		I <sub>S</sub> = -1.0 A		10			

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

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## N-CHANNEL TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

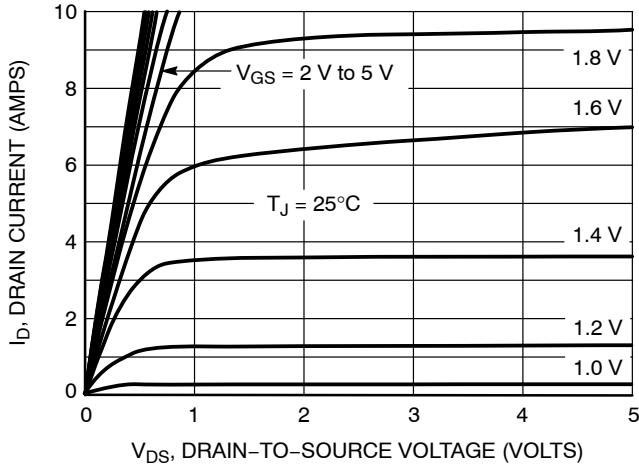


Figure 1. On-Region Characteristics

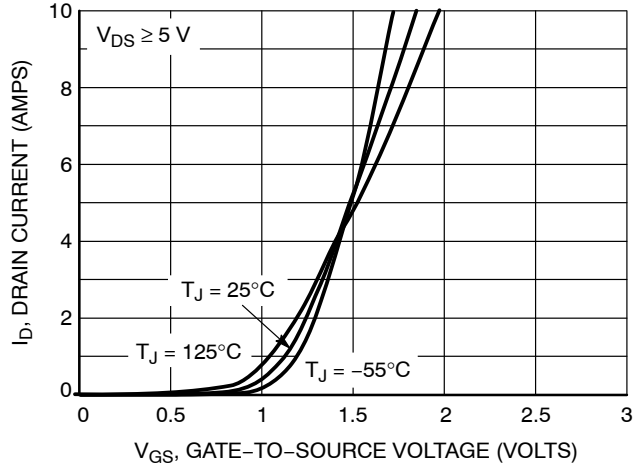


Figure 2. Transfer Characteristics

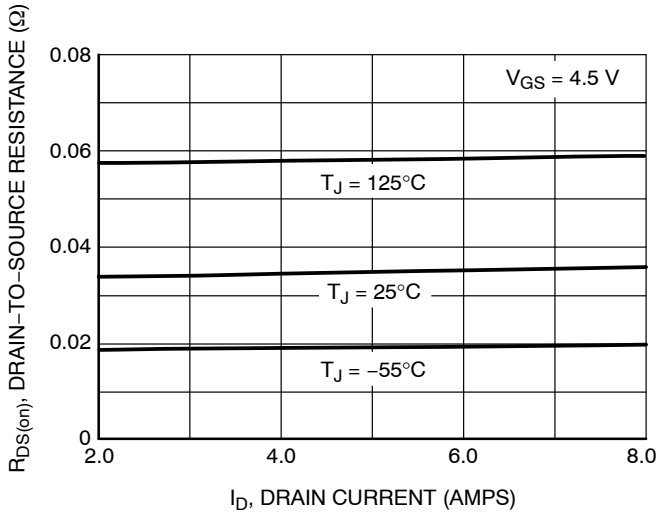


Figure 3. On-Resistance versus Drain Current

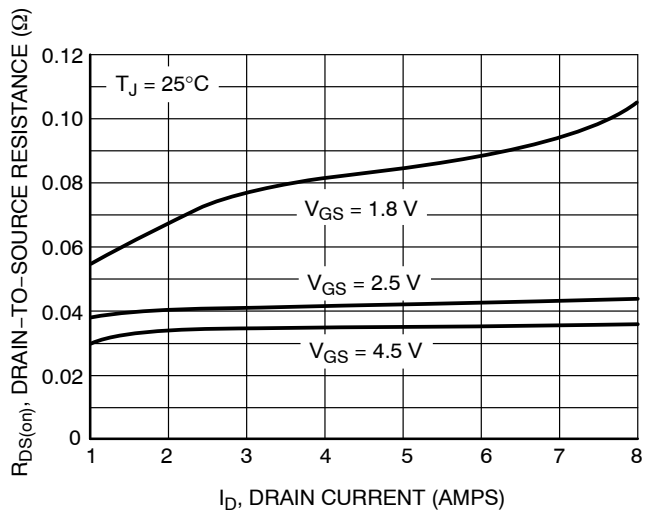


Figure 4. On-Resistance versus Drain Current and Gate Voltage

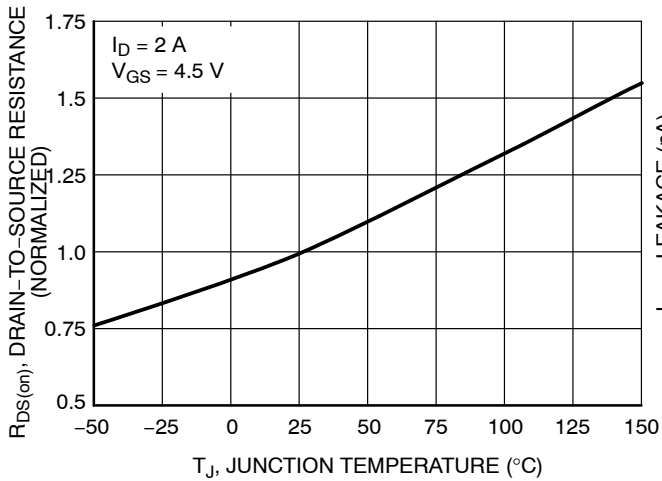


Figure 5. On-Resistance Variation with Temperature

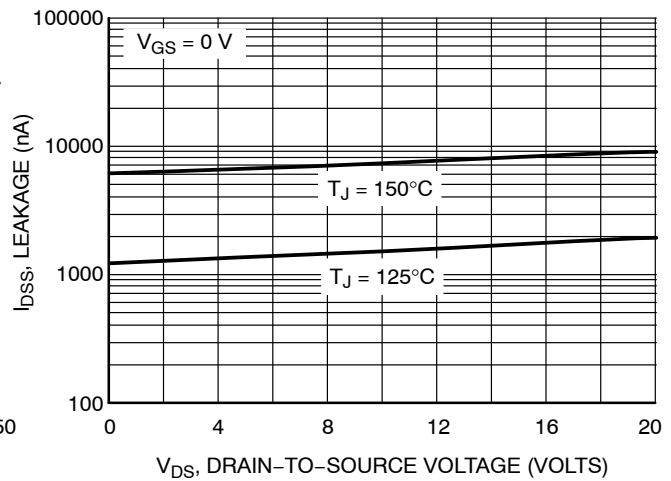


Figure 6. Drain-to-Source Leakage Current versus Voltage

# NTLJD3183CZ

## N-CHANNEL TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

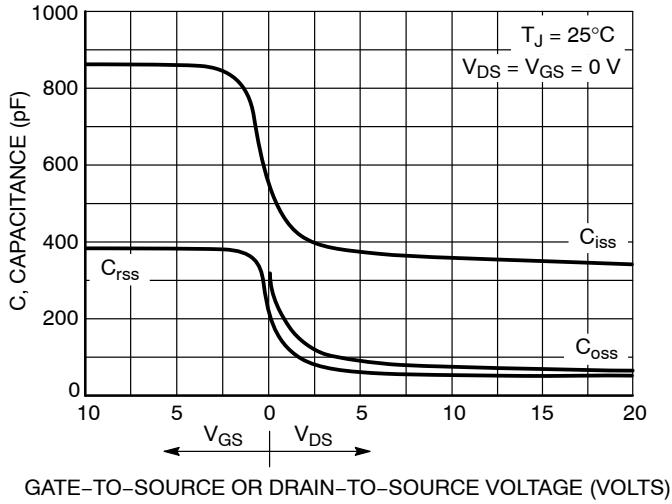


Figure 7. Capacitance Variation

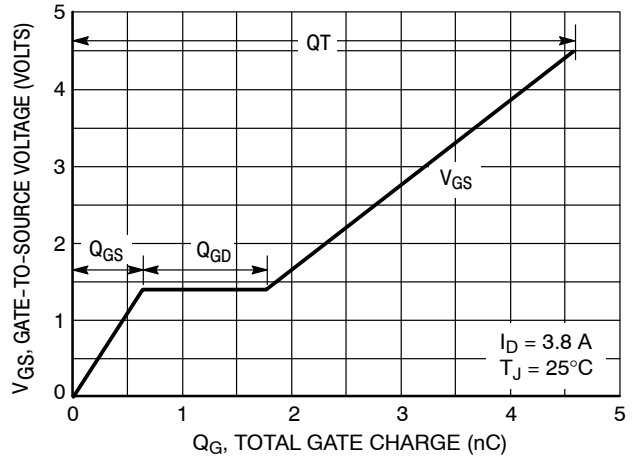


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

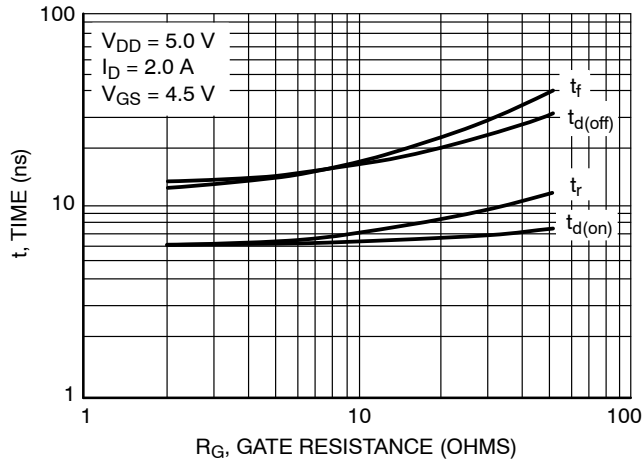


Figure 9. Resistive Switching Time Variation versus Gate Resistance

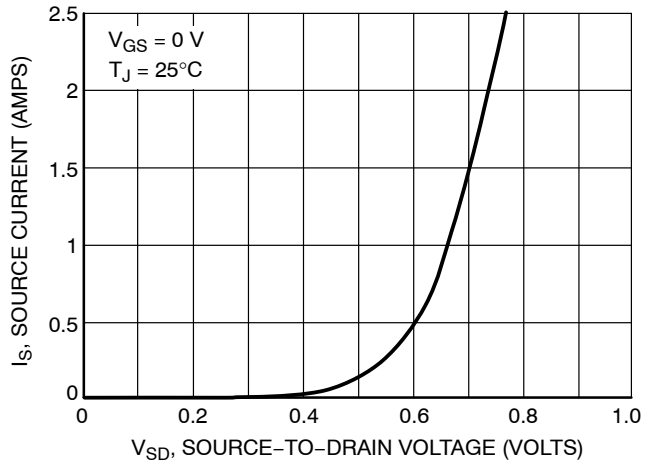


Figure 10. Diode Forward Voltage versus Current

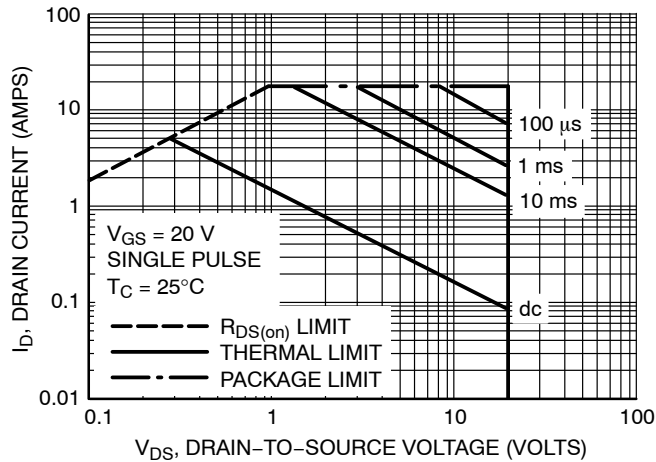
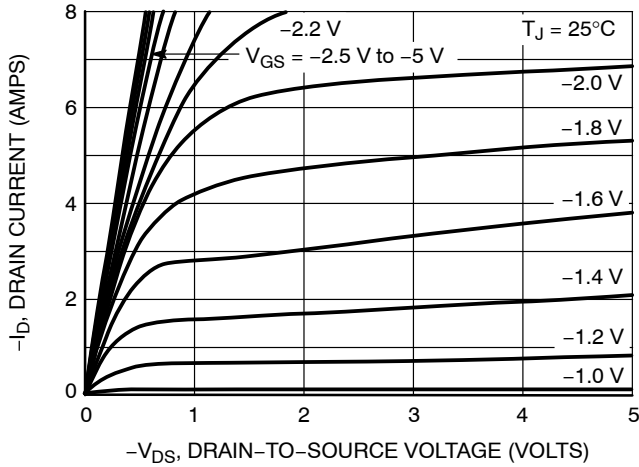


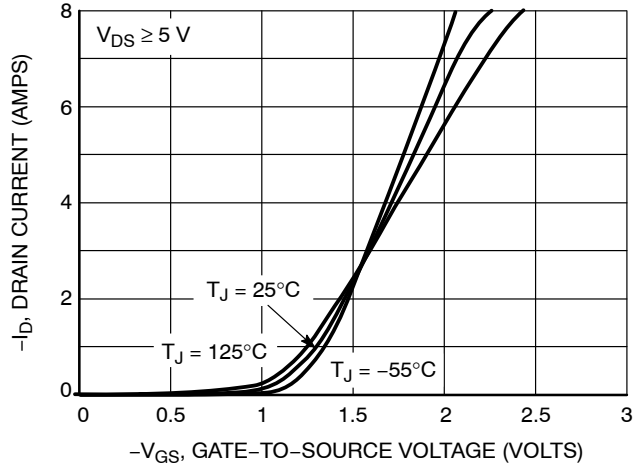
Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NTLJD3183CZ

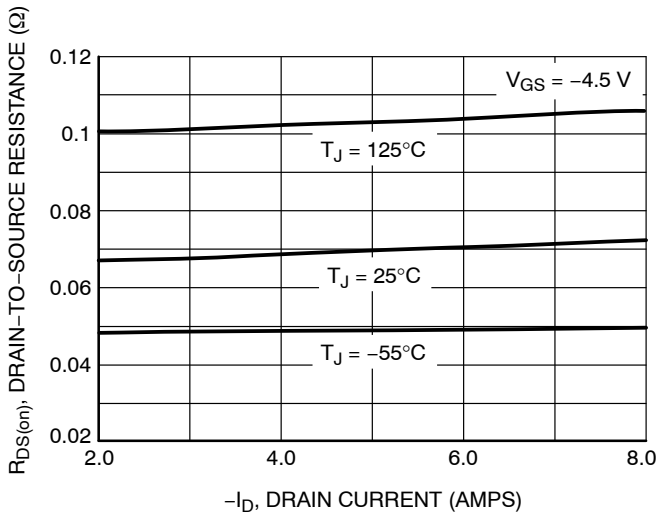
## P-CHANNEL TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)



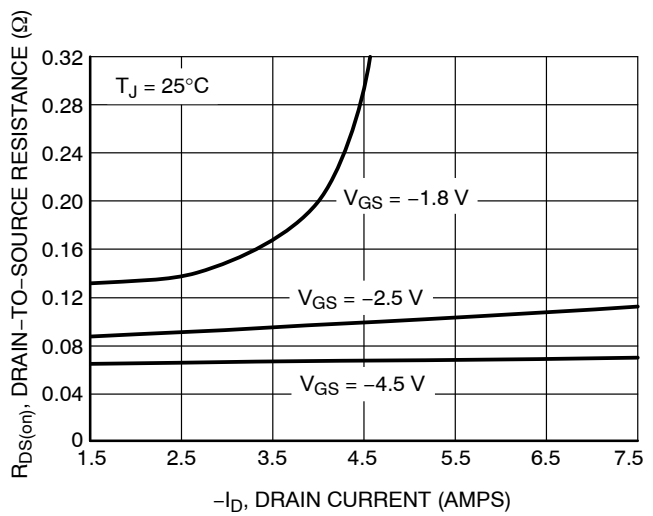
**Figure 12. On-Region Characteristics**



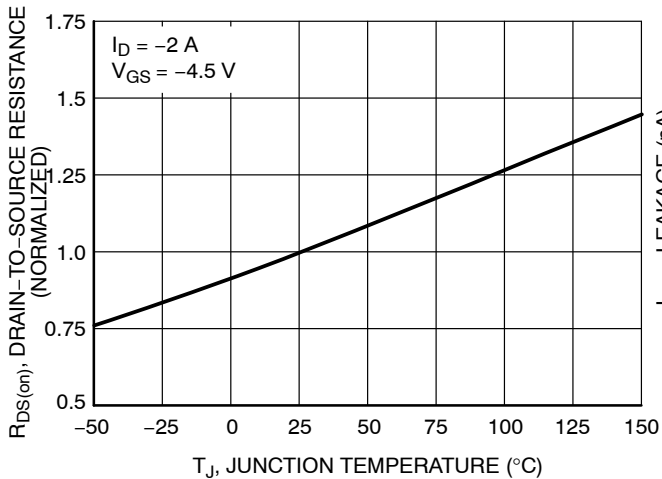
**Figure 13. Transfer Characteristics**



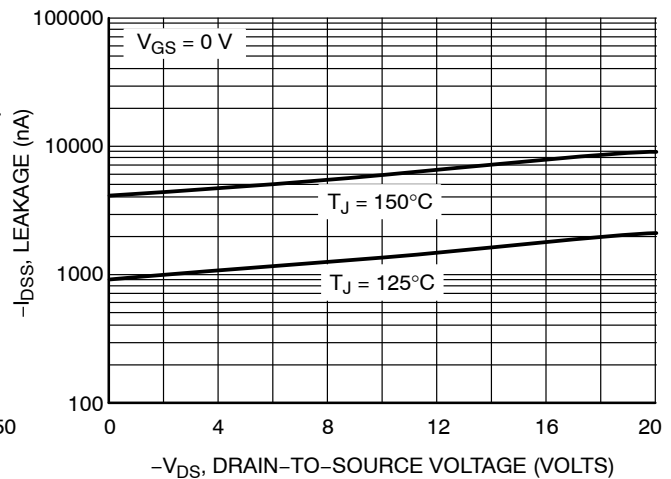
**Figure 14. On-Resistance versus Drain Current**



**Figure 15. On-Resistance versus Drain Current and Gate Voltage**



**Figure 16. On-Resistance Variation with Temperature**



**Figure 17. Drain-to-Source Leakage Current versus Voltage**

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## P-CHANNEL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

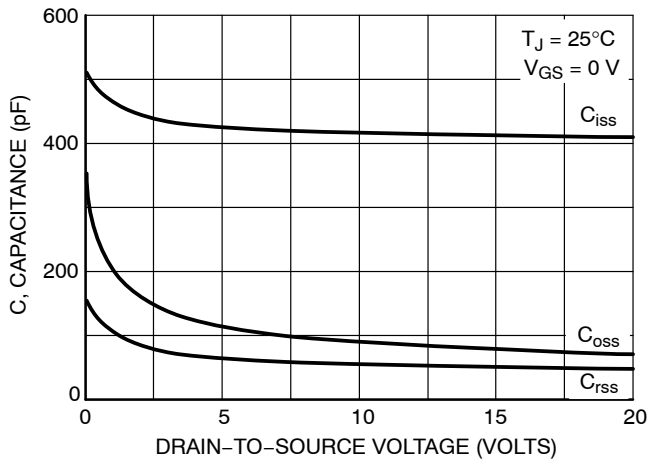


Figure 18. Capacitance Variation

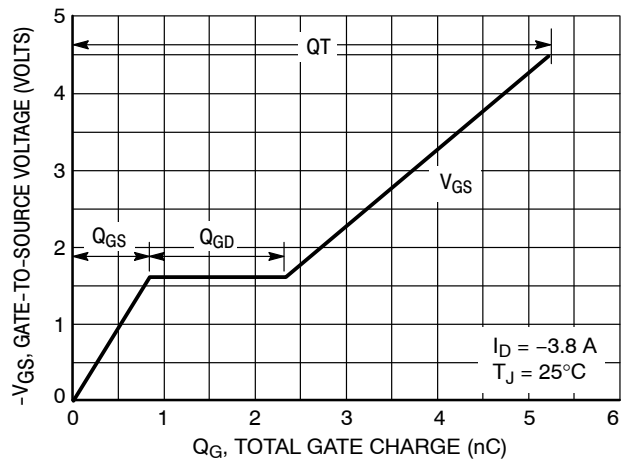


Figure 19. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

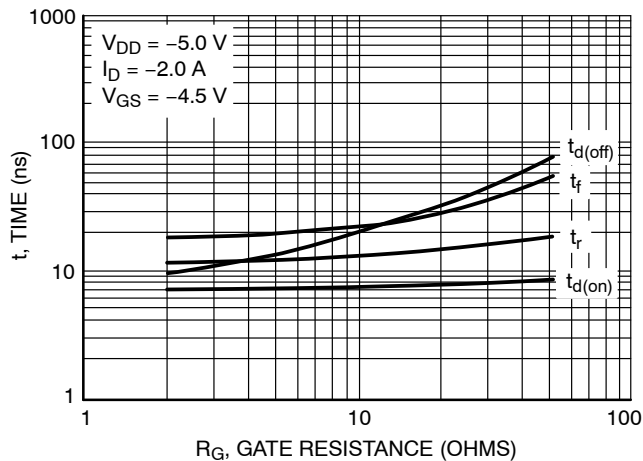


Figure 20. Resistive Switching Time Variation versus Gate Resistance

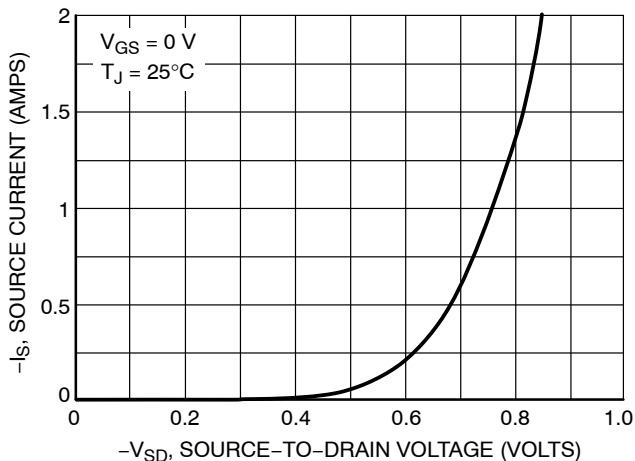


Figure 21. Diode Forward Voltage versus Current

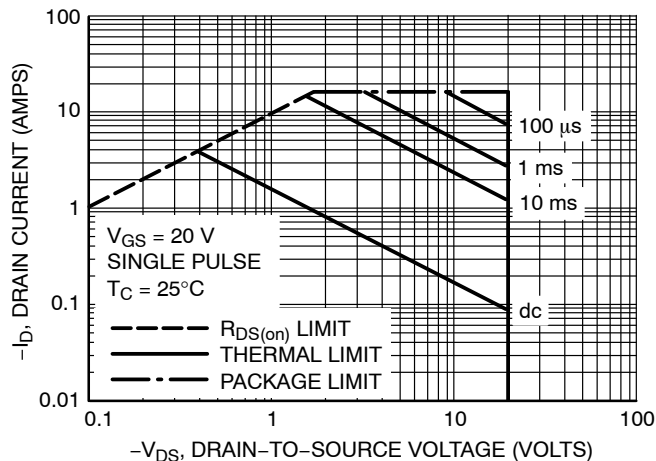


Figure 22. Maximum Rated Forward Biased Safe Operating Area

# NTLJD3183CZ

## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

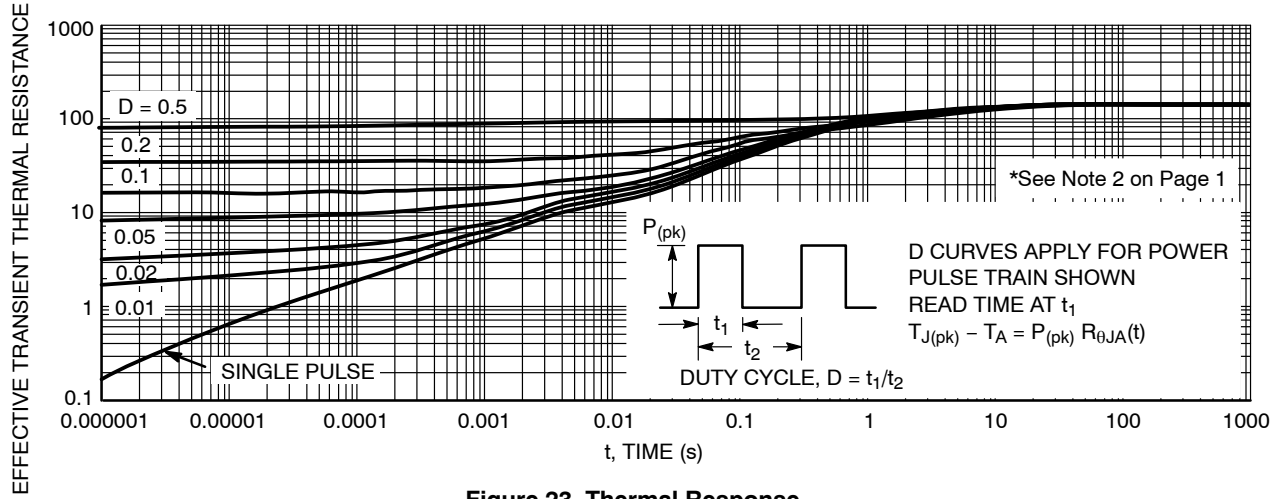
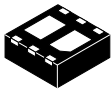


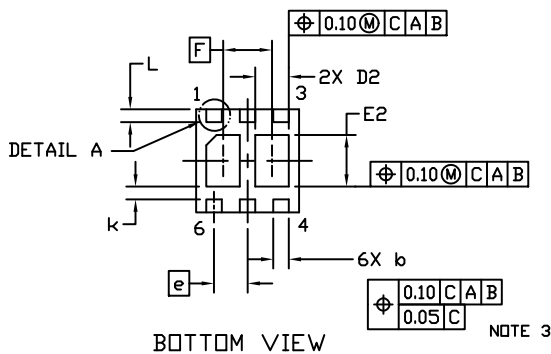
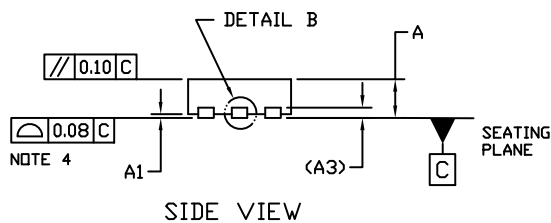
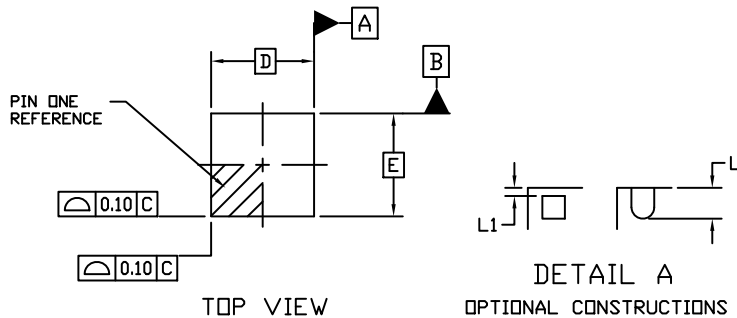
Figure 23. Thermal Response





**WDFN6 2x2, 0.65P**  
**CASE 506AN**  
**ISSUE H**

DATE 25 JAN 2022



**GENERIC MARKING DIAGRAM\***



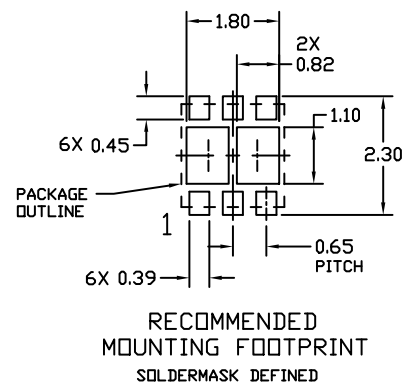
XX = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION **b** APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN.	MAX.
A	0.70	0.80
A1	0.00	0.05
A3	0.20 REF	
b	0.25	0.35
D	2.00 BSC	
D2	0.57	0.77
E	2.00 BSC	
E2	0.90	1.10
e	0.65 BSC	
F	0.95 BSC	
k	0.25 REF	
L	0.20	0.30
L1	---	0.10



<b>DOCUMENT NUMBER:</b>	<b>98AON20861D</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>WDFN6 2x2, 0.65P</b>	<b>PAGE 1 OF 1</b>

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